

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0017				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0020				
I _D (A)	200				
Configuration	Single				
Package	TO-263-7L				

FEATURES

• TrenchFET® power MOSFET

N-Channel MOSFET

- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ABSOLUTE MAXIMUM RATIN PARAMETER	,	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40		
Gate-Source Voltage		V _{GS}	± 20	·	
Continuous Drain Current	T _C = 25 °C a	I _D	200	A	
	T _C = 125 °C		193		
Continuous Source Current (Diode Condu	ction) ^a	I _S	200		
Pulsed Drain Current ^b		I _{DM}	600		
Single Pulse Avalanche Current		I _{AS}	95		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	451	mJ	
Martin as Brown Bloods attach	T _C = 25 °C	D	375	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	125		
Operating Junction and Storage Temperature Range		T _J , T _{stq}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W		
Junction-to-Case (Drain)		R_{thJC}	0.4	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static				l		I.		
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	200	-	=.	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0012	0.0017	Ω	
Drain-Source On-State Resistance a	В	V _{GS} = 10 V	I _D = 30 A, T _J = 125 °C	-	-	0.0028		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0034		
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0014	0.0020		
Forward Transconductance b	9fs	V _{DS} = 15 V, I _D = 30 A		-	181	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	8934	11 168	pF	
Output Capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	1592	1990		
Reverse Transfer Capacitance	C _{rss}			-	928	1160		
Total Gate Charge ^c	Q_g			-	194	291		
Gate-Source Charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 20 \text{ V}, I_D = 20 \text{ A}$	-	25	-	nC	
Gate-Drain Charge ^c	Q_{gd}			-	40	-		
Gate Resistance	R_g	f = 1 MHz		0.25	0.8	1.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V, } R_L = 1 \Omega$ $I_D \cong 20 \text{ A, } V_{GEN} = 10 \text{ V, } R_g = 1 \Omega$		-	22	33		
Rise Time ^c	t _r			-	17	26	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	70	105		
Fall Time ^c	t _f			-	16	24		
Source-Drain Diode Ratings and Chara	cteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	600	Α	
Forward Voltage	V_{SD}	I _F = 60 A, V _{GS} = 0 V		_	0.8	1.5	V	

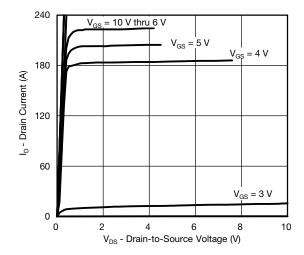
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

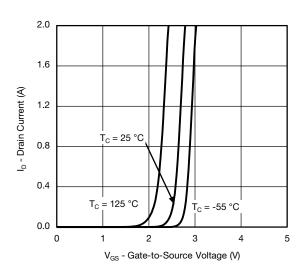
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



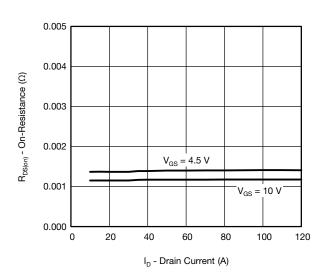
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



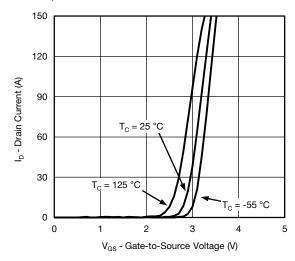
Output Characteristics



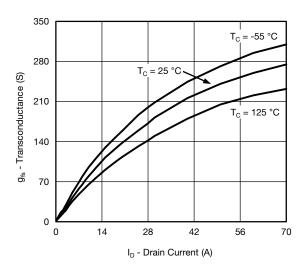
Transfer Characteristics



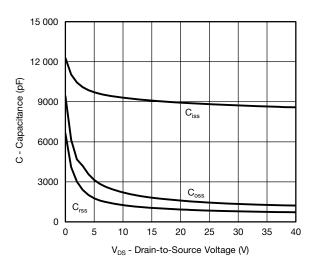
On-Resistance vs. Drain Current



Transfer Characteristics



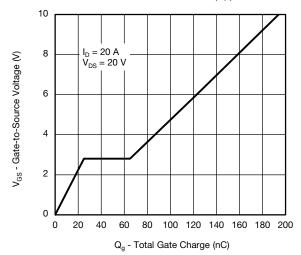
Transconductance



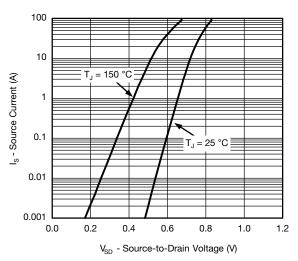
Capacitance



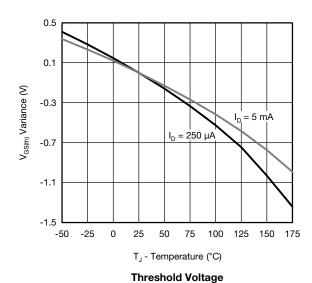
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

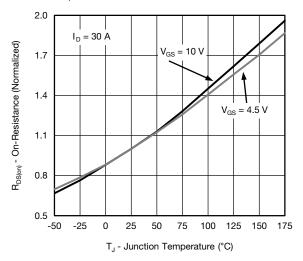


Gate Charge

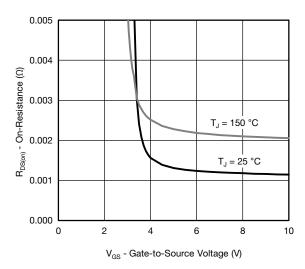


Source Drain Diode Forward Voltage

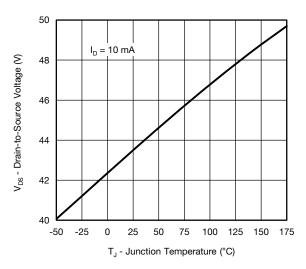




On-Resistance vs. Junction Temperature



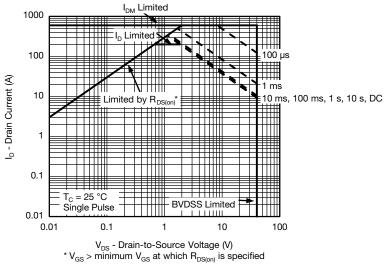
On-Resistance vs. Gate-to-Source Voltage



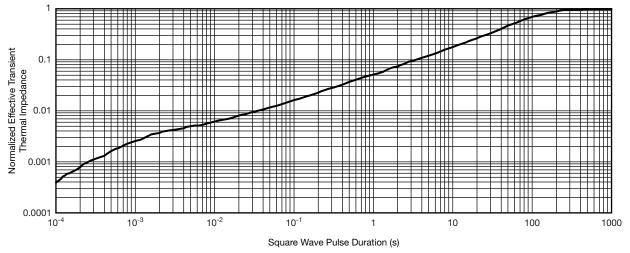
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



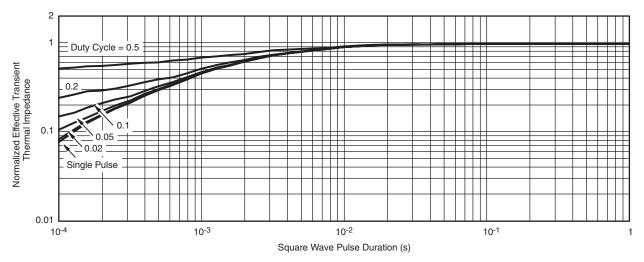
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg267058.



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REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
В	04-Aug-15	Revised R _g minimum limit		

Note

a. As of April 2014

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D²PAK / TO-263 and TO-262

Ordering codes for the SQ rugged series power MOSFETs in the D²PAK / TO-263 and TO-262 packages:

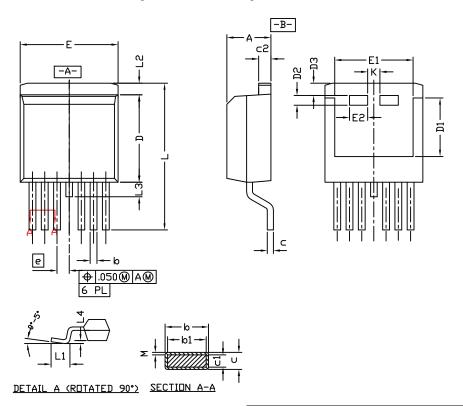
DATASHEET PART NUMBER	OLD ORDERING CODE a	NEW ORDERING CODE	
SQM100N04-2m7	SQM100N04-2M7-GE3	SQM100N04-2M7_GE3	
SQM100N10-10	SQM100N10-10-GE3	SQM100N10-10_GE3	
SQM110N05-06L	SQM110N05-06L-GE3	SQM110N05-06L_GE3	
SQM110P06-8m9L	SQM110P06-8M9L-GE3	SQM110P06-8M9L_GE3	
SQM120N02-1m3L	SQM120N02-1M3L-GE3	SQM120N02-1M3L_GE3	
SQM120N03-1m5L	SQM120N03-1M5L-GE3	SQM120N03-1M5L_GE3	
SQM120N04-1m7	SQM120N04-1M7-GE3	SQM120N04-1M7_GE3	
SQM120N04-1m7L	SQM120N04-1M7L-GE3	SQM120N04-1M7L_GE3	
SQM120N04-1m9	SQM120N04-1M9-GE3	SQM120N04-1M9_GE3	
SQM120N06-06	SQM120N06-06-GE3	SQM120N06-06_GE3	
SQM120N06-3m5L	SQM120N06-3M5L-GE3	SQM120N06-3M5L_GE3	
SQM120N10-09	SQM120N10-09-GE3	SQM120N10-09_GE3	
SQM120N10-3m8	SQM120N10-3M8-GE3	SQM120N10-3M8_GE3	
SQM120P04-04L	SQM120P04-04L-GE3	SQM120P04-04L_GE3	
SQM120P06-07L	SQM120P06-07L-GE3	SQM120P06-07L_GE3	
SQM120P10-10m1L	-	SQM120P10_10m1LGE3	
SQM200N04-1m1L	SQM200N04-1M1L-GE3	SQM200N04-1M1L_GE3	
SQM200N04-1m7L	SQM200N04-1M7L-GE3	SQM200N04-1M7L_GE3	
SQM200N04-1m8	SQM200N04-1M8-GE3	SQM200N04-1M8_GE3	
SQM25N15-52	SQM25N15-52-GE3	SQM25N15-52_GE3	
SQM35N30-97	SQM35N30-97-GE3	SQM35N30-97_GE3	
SQM40010EL	-	SQM40010EL_GE3	
SQM40N10-30	SQM40N10-30-GE3	SQM40N10-30_GE3	
SQM40N15-38	SQM40N15-38-GE3	SQM40N15-38_GE3	
SQM40P10-40L	SQM40P10-40L-GE3	SQM40P10-40L_GE3	
SQM47N10-24L	SQM47N10-24L-GE3	SQM47N10-24L_GE3	
SQM50020EL	-	SQM50020EL_GE3	
SQM50N04-4m0L	SQM50N04-4M0L-GE3	SQM50N04-4M0L_GE3	
SQM50N04-4m1	SQM50N04-4M1-GE3	SQM50N04-4M1_GE3	
SQM50P03-07	SQM50P03-07-GE3	SQM50P03-07_GE3	
SQM50P04-09L	SQM50P04-09L-GE3	SQM50P04-09L_GE3	
SQM50P06-15L	SQM50P06-15L-GE3	SQM50P06-15L_GE3	
SQM50P08-25L	SQM50P08-25L-GE3	SQM50P08-25L_GE3	
SQM60030E	-	SQM60030E_GE3	
SQM60N06-15	SQM60N06-15-GE3	SQM60N06-15_GE3	
SQM60N20-35	SQM60N20-35-GE3	SQM60N20-35_GE3	
SQM70060EL	- -	SQM70060EL_GE3	
SQM85N15-19	SQM85N15-19-GE3	SQM85N15-19_GE3	
SQV120N10-3m8	SQV120N10-3m8-GE3	SQV120N10-3m8 GE3	
SQV120N06-4m7L	521.221.13 6 525	SQV120N06-4m7L GE3	

Note

a. Old ordering code is obsolete and no longer valid for new orders



D²PAK (TO-263-7L) Case Outline



Notes

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIN	METERS	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c* SUB	0.012	0.018	0.305	0.457	
c* SUM	0.022	0.028	0.559	0.711	
c1	0.018	0.025	0.457	0.635	
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
Е	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.072	0.078	1.829	1.981	
е	0.050	BSC	1.27 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254	BSC	
М	-	0.002	-	0.050	
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006					

1 Document Number: 63782



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